

*ABSTRACT AMENDMENTS*

Replace the Abstract with:

ABSTRACT

A method of fabricating a thin-film of a semiconductor material includes: a scanning irradiation step of, in order to form a polycrystalline silicon film on the surface of a substrate, focusing first pulse laser light having a visible wavelength into a line shape having an intensity distribution of an approximately Gaussian shape in a width direction on the surface of ~~said the~~ substrate and applying the light such that the line shape is shifted in the width direction; an edge processing step of, after performing ~~said the~~ scanning irradiation step in one position in one direction, applying second pulse laser light having an ultraviolet wavelength to an end region of an edge parallel to ~~said the~~ width direction of a region ~~(36)~~ having undergone the scanning irradiation; and a step of applying ~~said the~~ scanning irradiation step again to cover a region that is adjacent to the region ~~(36)~~ covered by ~~said the~~ scanning irradiation step as well as overlaps ~~said the~~ end region having undergone ~~said the~~ edge processing step.